

N-Ch MOSFET

General Description

The WSK220N04 is the highest performance trench N-Ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSK220N04 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

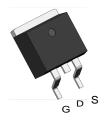
Product Summery

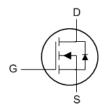
BVDSS	RDSON	ID	
40V	$2.5 m\Omega$	220A	

Applications

- Switching application
- Power Management for Inverter Systems.

TO-263 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit		
Common I	Ratings (T _C =25°C Unless Otherwise Noted)			•	
V _{DSS}	Drain-Source Voltage		40	V	
V_{GSS}	Gate-Source Voltage		±20	_	
TJ	Maximum Junction Temperature		175	℃	
T _{STG}	Storage Temperature Range		-55 to 175	°C	
I _S	Diode Continuous Forward Current T _C =25℃		208	А	
Mounted o	on Large Heat Sink			•	
I _{DM}	Pulsed Drain Current *	T _C =25℃	760 ^{1,2}	А	
1	Continuous Drain Current	T _C =25℃	220		
l _D		T _C =100°C	139	A	
P _D	Maximum Power Dissipation	T _C =25℃	218	w	
		T _C =100℃	109	VV	
$R_{\theta JC}$	Thermal Resistance-Junction to Case		0.55	°C/W	
$R_{ heta JA}$	Thermal Resistance-Junction to Ambient		62.5		
Avalanche	Ratings			•	
E _{AS}	Avalanche Energy, Single Pulsed	L=0.5mH	1.4 ^{1,2}	J	

NOTE:

1,Repetitive rating; pulse width limited by junction temperatur

2,Drain current is limited by junction temperature



Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

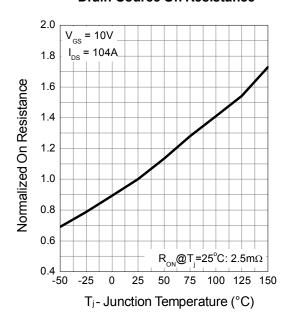
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit	
Static Cha	racteristics	•	1				
BV _{DSS}	Drain-Source Breakdown Voltage V _{GS} =0V, I _{DS} =250μA		40	-	-	V	
	Zero Gate Voltage Drain Current	V _{DS} =40V, V _{GS} =0V	-	-	1	^	
I _{DSS}		T _J =85℃	-	-	10	μΑ	
V _{GS(th)}	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	2.0	3.0	4.0	V	
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA	
R _{DS(ON)} *	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =104A	-	2.5	3.2	mΩ	
Diode Cha	racteristics	•	•				
V _{SD} *	Diode Forward Voltage	vard Voltage I _{SD} =104 A, V _{GS} =0V		0.8	1.2	V	
t _{rr}	Reverse Recovery Time	I_{SD} =104A, dI_{SD} /	-	36	-	ns	
Q _{rr}	Reverse Recovery Charge	dt=100A/μs	-	59	-	nC	
Dynamic C	Characteristics				•		
R_G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz	-	1.0	-	Ω	
C _{iss}	Input Capacitance	V _{GS} =0V,	-	5710	-	pF	
C _{oss}	Output Capacitance	V _{DS} =25V,	-	1463	-		
C _{rss}	Reverse Transfer Capacitance	Frequency=1.0MHz	-	595	-		
t _{d(ON)}	Turn-on Delay Time		-	34	-		
T _r	Turn-on Rise Time	V_{DD} =20V, R_{G} =6 Ω , I_{DS} =104A, V_{GS} =10V ,	-	19	-	no	
t _{d(OFF)}	Turn-off Delay Time	======================================	-	44	-	ns	
T _f	Turn-off Fall Time		-	61	-		
Gate Char	ge Characteristics	•	7	Ī	Ī	-	
Q _g	Total Gate Charge		-	156	-		
Q _{gs}	Gate-Source Charge	V_{DS} =32V, V_{GS} =10V, I_{DS} =104A	-	28	-	nC	
Q_{gd}	Gate-Drain Charge		-	65	-		

Note * : Pulse test ; pulse width $\leq\!300\mu s,$ duty cycle $\!\leq\!2\%.$

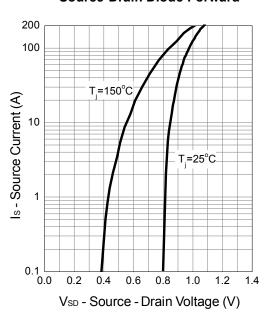


Typical Characteristics

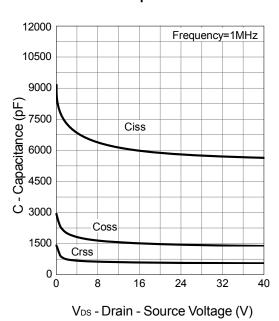
Drain-Source On Resistance



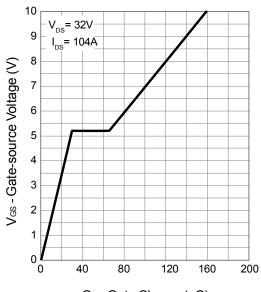
Source-Drain Diode Forward



Capacitance

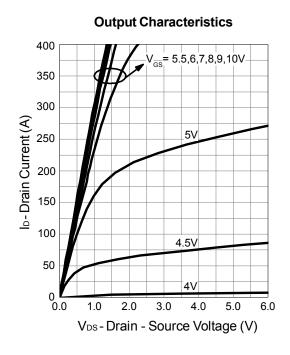


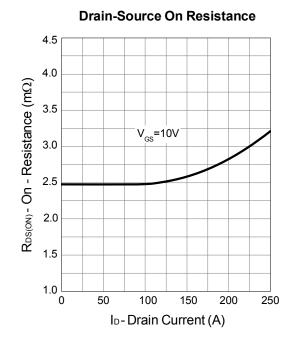
Gate Charge

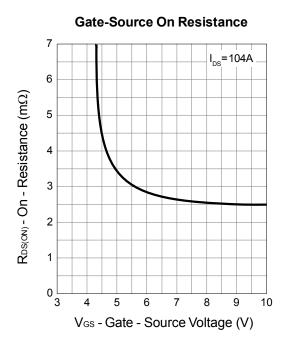


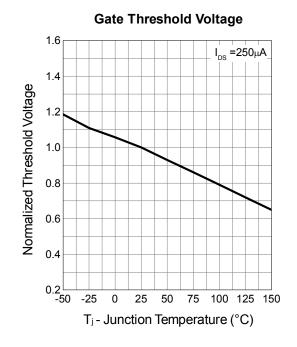


Typical Characteristics



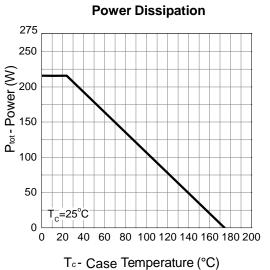


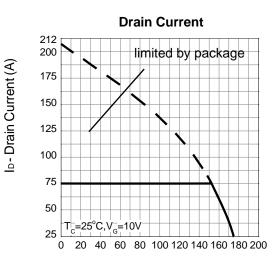




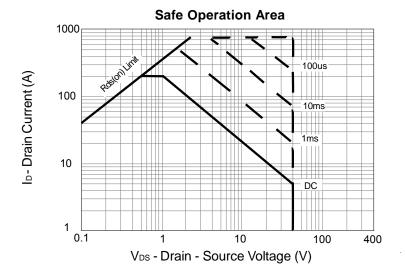


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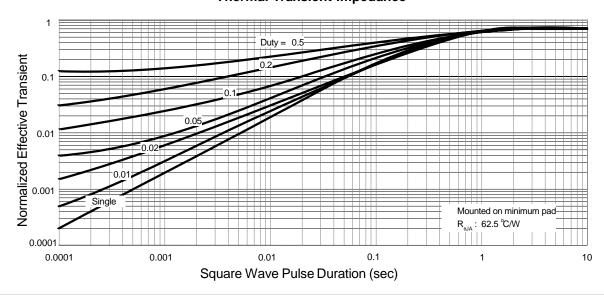




T_c-Case Temperature (°C)

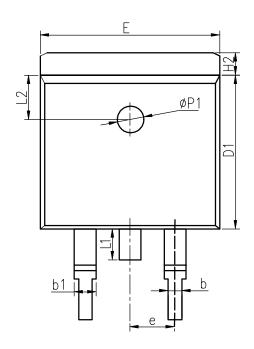


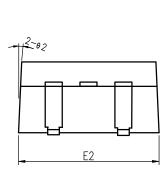
Thermal Transient Impedance

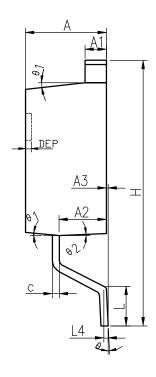




TO-263-2L







COMMON DIMENSIONS

SYMBOL	MM			INCH			
STIVIBUL	MIN	NOM	MAX	MIN	NOM	MAX	
Α	4.40	4.57	4.70	0.173	0.180	0.185	
A1	1.22	1.27	1.32	0.048	0.050	0.052	
A2	2.59	2.69	2.79	0.102	0.106	0.110	
A3	0.00	0.10	0.20	0.000	0.004	0.008	
b	0.77	0.813	0.90	0.030	0.032	0.035	
b1	1.20	1.270	1.36	0.047	0.050	0.054	
С	0.34	0.381	0.47	0.013	0.015	0.019	
D1	8.60	8.70	8.80	0.339	0.343	0.346	
Е	10.00	10.16	10.26	0.394	0.400	0.404	
E2	10.00	10.10	10.20	0.394	0.398	0.402	
е	2.54 BSC			0.100 BSC			
Н	14.70	15.10	15.50	0.579	0.594	0.610	
H2	1.17	1.27	1.40	0.046	0.050	0.055	
L	2.00	2.30	2.60	0.079	0.091	0.102	
L1	1.45	1.55	1.70	0.057	0.061	0.067	
L2		2.50	REF		0.098 REF		
L4	0.25 BSC 0.			0.010	0 BSC		
	0°	5°	8°	0°	5°	8°	
1	5°	7°	9°	5°	7°	9°	
2	1°	3°	5°	1°	3°	5°	
ФР1	1.40	1.50	1.60	0.055	0.059	0.063	
DEP	0.05	0.10	0.20	0.002	0.004	0.008	



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